CY62177DV30 MoBL®

32-Mbit (2M × 16) Static RAM

Features

- Very high speed: 55 ns
- Wide voltage range: 2.20 V–3.60 V
- Ultra-low active power
  - Typical active current: 2 mA at f = 1 MHz
  - Typical active current: 15 mA at f = f_{max}
- Ultra low standby power
- Easy memory expansion with $\overline{CE}_1$, CE_2 and $\overline{OE}$ features
- Automatic power-down when deselected
- Complementary metal oxide semiconductor (CMOS) for optimum speed/power
- Packages offered in a 48-ball fine ball grid array (FBGA)

Functional Description

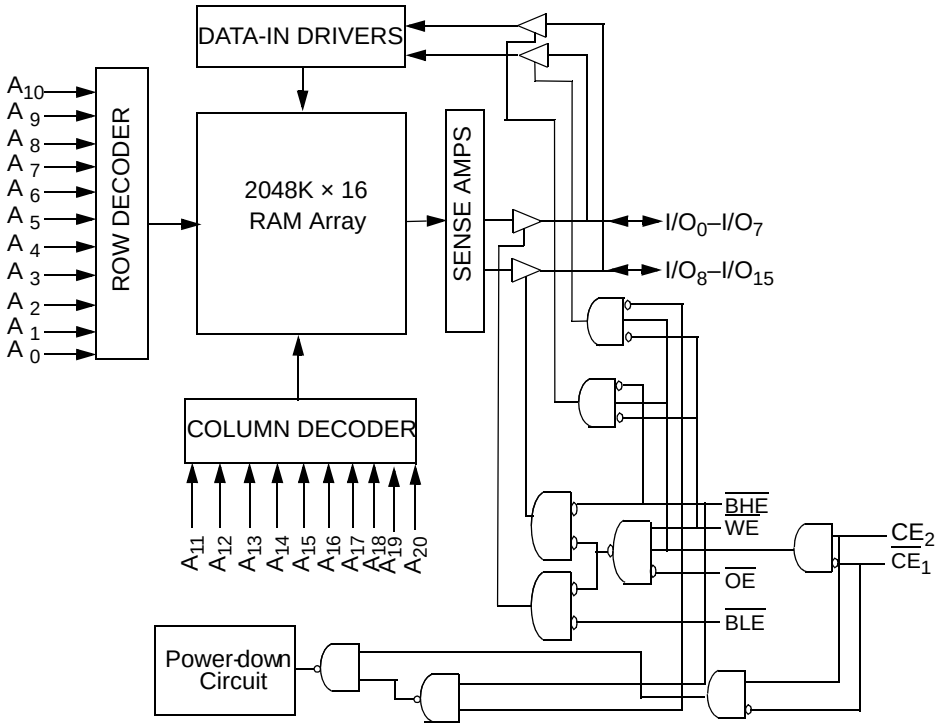
The CY62177DV30 is a high-performance CMOS static RAM organized as 2M words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones.The device also has an automatic power-down feature that significantly reduces power consumption. The device can also be put into standby mode when deselected ($\overline{CE}_1$ HIGH or CE_2 LOW or both $\overline{BHE}$ and $\overline{BLE}$ are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}_1$HIGH or CE_2 LOW), outputs are disabled ($\overline{OE}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}_1$ LOW, CE_2 HIGH and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enables ($\overline{CE}_1$ LOW and CE_2 HIGH) and Write Enable ($\overline{WE}$) input LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{20}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{20}).

Reading from the device is accomplished by taking Chip Enables ($\overline{CE}_1$ LOW and CE_2 HIGH) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table for a complete description of read and write modes.

For a complete list of related documentation, click here.

Logic Block Diagram

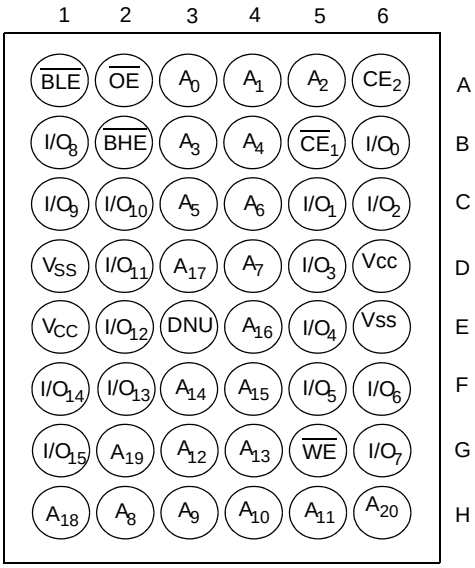


Contents

Pin Configuration **3**
Product Portfolio **3**
Maximum Ratings **4**
Operating Range **4**
Electrical Characteristics **4**
Capacitance **5**
Thermal Resistance **5**
AC Test Loads and Waveforms **5**
Data Retention Characteristics **6**
Data Retention Waveform **6**
Switching Characteristics **7**
Switching Waveforms **8**
Truth Table **11**
Ordering Information **12**
Ordering Code Definitions 12
Package Diagram **13**
Acronyms **14**
Document Conventions **14**
Units of Measure 14
Document History Page **15**
Sales, Solutions, and Legal Information **17**
Worldwide Sales and Design Support 17
Products 17
PSoC®Solutions 17
Cypress Developer Community 17
Technical Support 17

Pin Configuration

Figure 1. 48-ball FBGApinout (Top View) [1]



Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC}(mA)				Standby I_{SB2}(µA)	
					f = 1 MHz		f = f_{max}			
	Min	Typ[2]	Max		Typ[2]	Max	Typ[2]	Max	Typ[2]	Max
CY62177DV30LL	2.2	3.0	3.6	55	2	4	15	30	5	50

Notes
1. DNU pins have to be left floating or tied to Vss to ensure proper application.
2. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ.)}$, T_A = 25 °C.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature ..... –65 °C to + 150 °C

Ambient temperature with power applied ..... –55 °C to + 125 °C

Supply voltage to ground potential ..... –0.3 V to V_{CC} + 0.3 V

DC voltage applied to outputs in High Z state [3, 4] ..... –0.3 V to V_{CC} + 0.3 V

DC input voltage[3, 4] ..... –0.3 V to V_{CC} + 0.3 V

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage (per MIL-STD-883, method 3015) ..... >2001 V

Latch-up current ..... >200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC}[5]
CY62177DV30LL	Industrial	–40 °C to +85 °C	2.20 V to 3.60 V

Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		Min	Typ[6]	Max	Unit
V_{OH}	Output HIGH voltage	I_{OH} = –0.1 mA	V_{CC} = 2.20 V	2.0	–	–	V
		I_{OH} = –1.0 mA	V_{CC} = 2.70 V	2.4	–	–	V
V_{OL}	Output LOW voltage	I_{OL} = 0.1 mA	V_{CC} = 2.20 V	–	–	0.4	V
		I_{OL} = 2.1 mA	V_{CC} = 2.70 V	–	–	0.4	V
V_{IH}	Input HIGH voltage	V_{CC} = 2.2 V to 2.7 V		1.8	–	V_{CC} + 0.3 V	V
		V_{CC} = 2.7 V to 3.6 V		2.2	–	V_{CC} + 0.3 V	V
V_{IL}	Input LOW voltage	V_{CC} = 2.2 V to 2.7 V		–0.3	–	0.6	V
		V_{CC} = 2.7 V to 3.6 V		–0.3	–	0.8	V
I_{IX}	Input leakage current	GND ≤ V_I ≤ V_{CC}		–1	–	+1	µA
I_{OZ}	Output leakage current	GND ≤ V_O ≤ V_{CC}, output disabled		–1	–	+1	µA
I_{CC}	V_{CC} operating supply current	f = f_{MAX} = 1/t_{RC}	V_{CC} = V_{CCmax}, I_{OUT} = 0 mA CMOS levels	–	15	30	mA
		f = 1 MHz			2	4	mA
I_{SB1}	Automatic CE power-down current – CMOS inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2 V, CE_2 < 0.2 V, V_{IN} ≥ V_{CC} – 0.2 V, V_{IN} ≤ 0.2 V, f = f_{MAX} (address and data only), f = 0 ($\overline{OE}$, $\overline{WE}$, $\overline{BHE}$ and $\overline{BLE}$), V_{CC} = 3.60 V		–	5	100	µA
I_{SB2}	Automatic CE power-down current – CMOS inputs	$\overline{CE}_1$ ≥ V_{CC} – 0.2 V, CE_2 < 0.2 V, V_{IN} ≥ V_{CC} – 0.2 V or V_{IN} ≤ 0.2 V, f = 0, V_{CC} = 3.60 V		–	5	50	µA

Notes

3. $V_{IL(min.)}$ = –2.0 V for pulse durations less than 20 ns.
4. $V_{IH(Max)}$ = V_{CC} + 0.75 V for pulse durations less than 20 ns.
5. Full device AC operation requires linear V_{CC} ramp from 0 to $V_{CC(min)}$ ≥ 500 µs.
6. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = $V_{CC(typ.)}$, T_A = 25 °C.

Capacitance

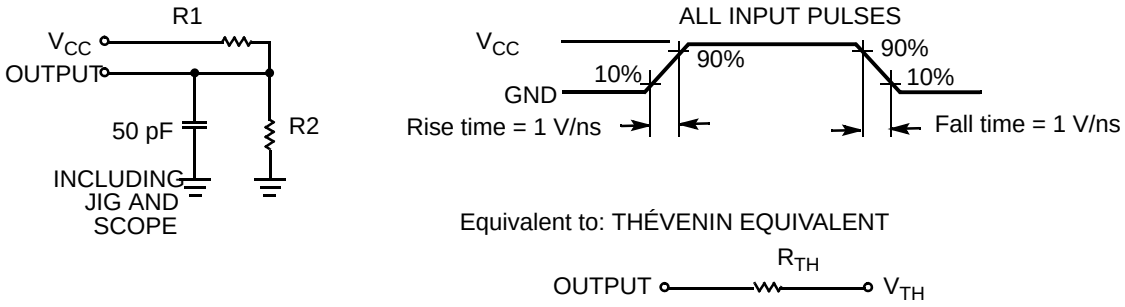
Parameter [7]	Description	Test Conditions	Max.	Unit
C_{IN}	Input capacitance	T_A = 25 °C, f = 1 MHz, $V_{CC} = V_{CC(typ)}$	12	pF
C_{OUT}	Output capacitance		12	pF

Thermal Resistance

Parameter [7]	Description	Test Conditions	BGA	Unit
θ_{JA}	Thermal resistance (junction to ambient)	Still Air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	46.31	°C/W
θ_{JC}	Thermal resistance (junction to case)		3.5	°C/W

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms



Parameters	2.5 V (2.2 V to 2.7 V)	3.0 V (2.7 V to 3.6 V)	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R_{TH}	8000	645	Ω
V_{TH}	1.20	1.75	V

Note
7. Tested initially and after any design or process changes that may affect these parameters.

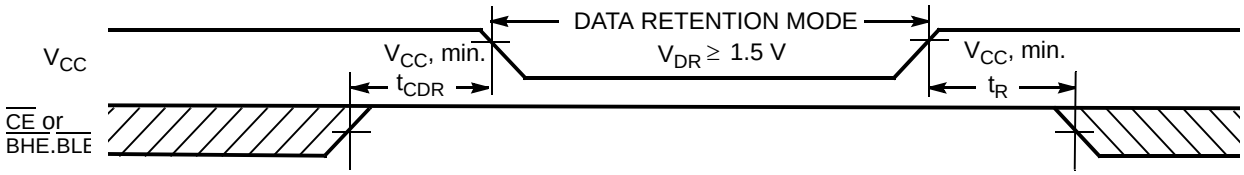
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Typ[9]	Max	Unit
V_{DR}	V_{CC} for data retention		1.5	–	–	V
I_{CCDR}	Data retention current	V_{CC}= 1.5 V $\overline{CE}_1 \geq V_{CC} - 0.2$ V, $CE_2 < 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V	–	–	25	µA
t_{CDR}[8]	Chip deselect to data retention time		0	–	–	ns
t_R[10]	Operation recovery time		55	–	–	ns

Data Retention Waveform

Figure 3. Data Retention Waveform [11, 12]



Notes
8. Tested initially and after any design or process changes that may affect these parameters.
9. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ.)}$, T_A = 25 °C
10. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} \geq 100$ µs or stable at $V_{CC(min.)} \geq 100$ µs.

Switching Characteristics

Over the Operating Range

Parameter [12, 13]	Description	Min	Max	Unit
Read Cycle				
t_{RC}	Read cycle time	55	–	ns
t_{AA}	Address to data valid	–	55	ns
t_{OHA}	Data hold from address change	10	–	ns
t_{ACE}	$\overline{CE}$ LOW to data valid	–	55	ns
t_{DOE}	$\overline{OE}$ LOW to data valid	–	25	ns
t_{LZOE}	$\overline{OE}$ LOW to LOW Z[14]	5	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[14, 15]	–	20	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[14]	10	–	ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[14, 15]	–	20	ns
t_{PU}	$\overline{CE}$ LOW to power-up	0	–	ns
t_{PD}	$\overline{CE}$ HIGH to power-down	–	55	ns
t_{DBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to data valid	–	55	ns
t_{LZBE}	$\overline{BLE}$/$\overline{BHE}$ LOW to Low Z[14]	10	–	ns
t_{HZBE}	$\overline{BLE}$/$\overline{BHE}$ HIGH to HIGH Z[14, 15]	–	20	ns
Write Cycle [16, 17]				
t_{WC}	Write cycle time	55	–	ns
t_{SCE}	$\overline{CE}$ LOW to write end	40	–	ns
t_{AW}	Address set-up to write end	40	–	ns
t_{HA}	Address hold from write end	0	–	ns
t_{SA}	Address set-up to write start	0	–	ns
t_{PWE}	$\overline{WE}$ pulse width	40	–	ns
t_{BW}	$\overline{BLE}$/$\overline{BHE}$ LOW to write end	40	–	ns
t_{SD}	Data set-up to write end	25	–	ns
t_{HD}	Data hold from write end	0	–	ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[14, 15]	–	20	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[14]	10	–	ns

Notes

11. $\overline{BHE}$.$\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Chip can be deselected by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.
12. $\overline{CE}$ is the logical combination of $\overline{CE_1}$ and CE_2. When $\overline{CE_1}$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE_1}$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
13. Test conditions for all parameters other than tri-state parameters assume signal transition time of 1 ns/V, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the “AC Test Loads and Waveforms” section.
14. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
15. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
16. The internal Write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.
17. The minimum write cycle pulse width for Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) should be equal to the sum of t_{SD} and t_{HZWE}.

Switching Waveforms

Figure 4. Read Cycle No. 1 (Address Transition Controlled) [18, 19, 20]

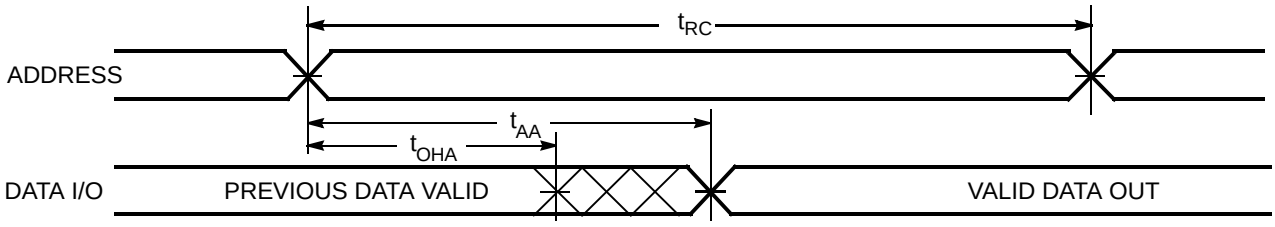
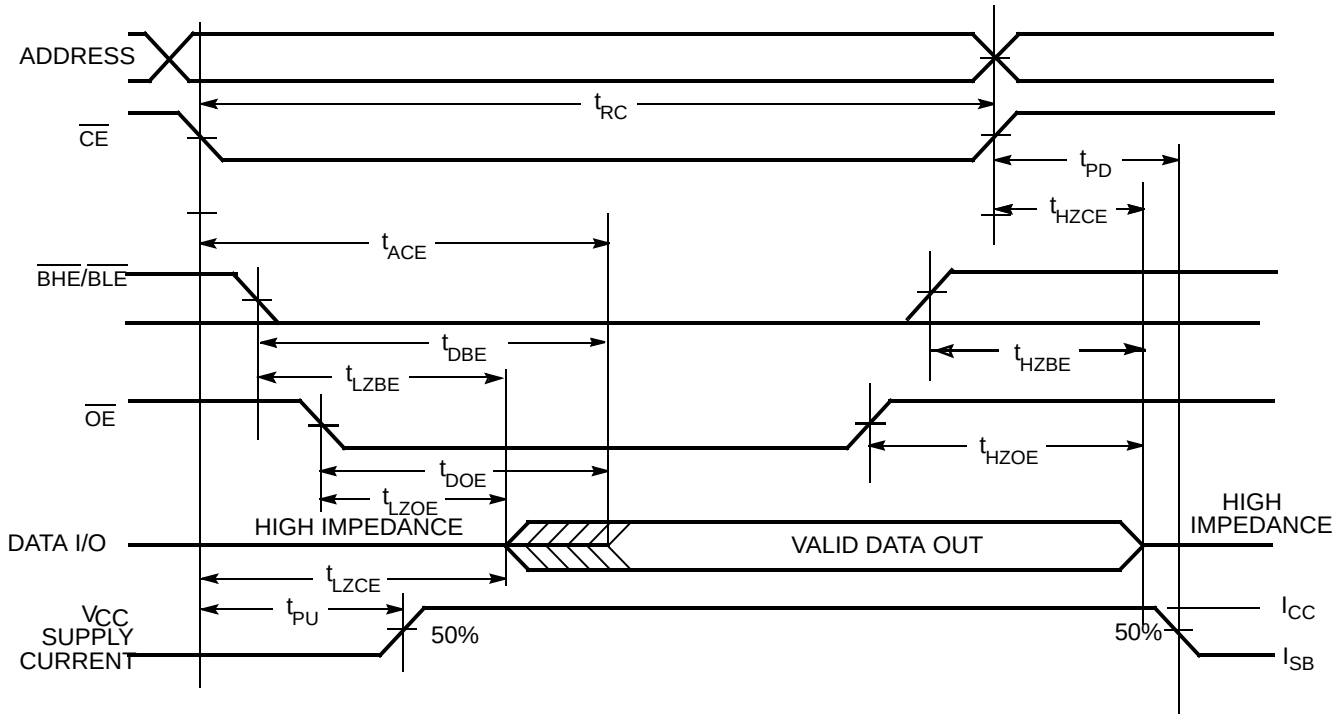


Figure 5. Read Cycle No. 2 ($\overline{OE}$ Controlled) [18, 20, 21, 22]



Notes
18. All Read/Write switching waveforms are shown for 16-bit data transactions only.
19. The device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}.
20. $\overline{WE}$ is HIGH for read cycle.
21. Address valid prior to or coincident with $\overline{CE}$, $\overline{BHE}$, $\overline{BLE}$ transition LOW.
22. $\overline{CE}$ is the logical combination of $\overline{CE_1}$ and CE_2. When $\overline{CE_1}$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE_1}$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.

Switching Waveforms (continued)

Figure 6. Write Cycle No. 1 (WE Controlled) [23, 24, 25, 26, 27, 28]

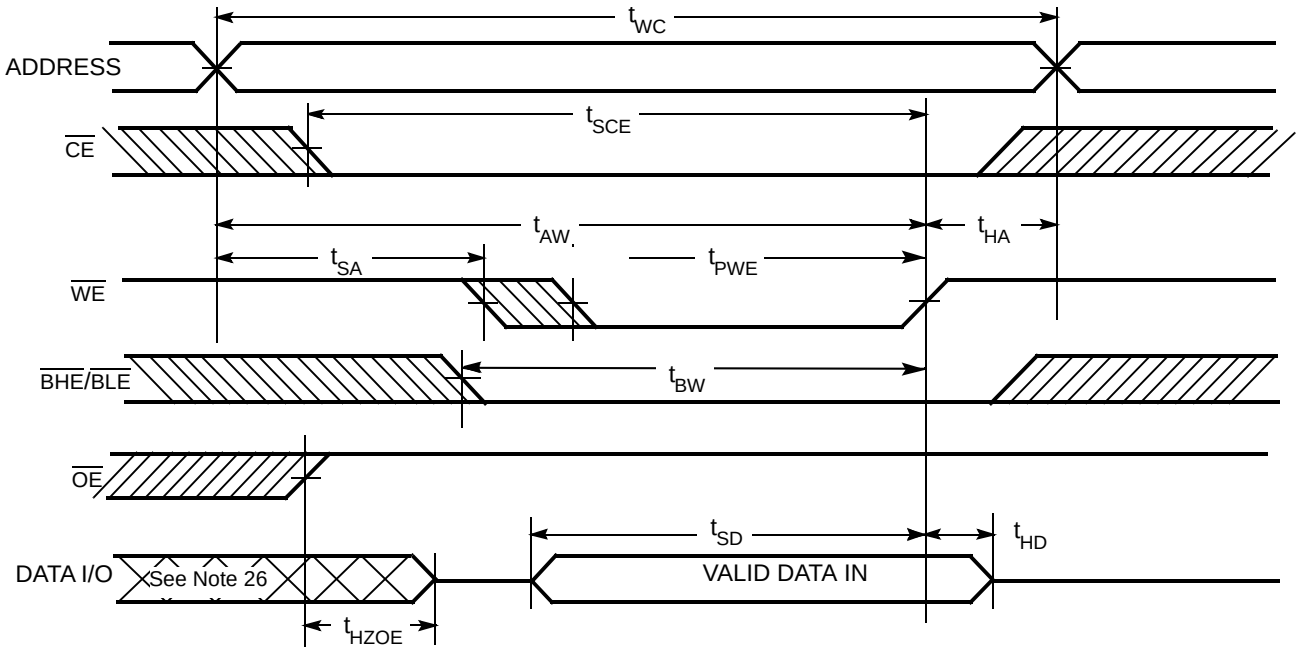
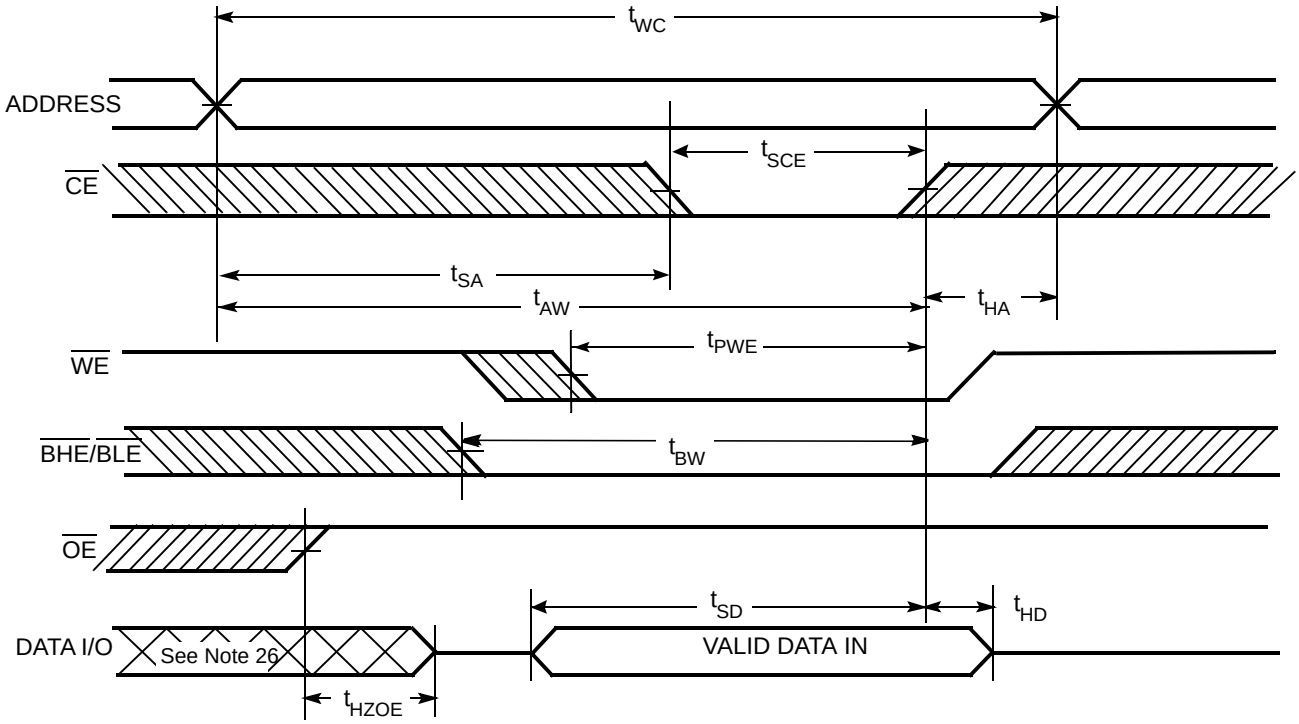


Figure 7. Write Cycle No. 2 (CE Controlled) [23, 24, 25, 26, 27, 28]



Notes

23. All Read/Write switching waveforms are shown for 16-bit data transactions only.
24. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
25. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high-impedance state.
26. During this period, the I/Os are in output state and input signals should not be applied.
27. $\overline{CE}$ is the logical combination of $\overline{CE_1}$ and CE_2. When $\overline{CE_1}$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE_1}$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
28. The internal Write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms (continued)

Figure 8. Write Cycle No. 3 (WE Controlled, OE LOW) [29, 30, 31, 32]

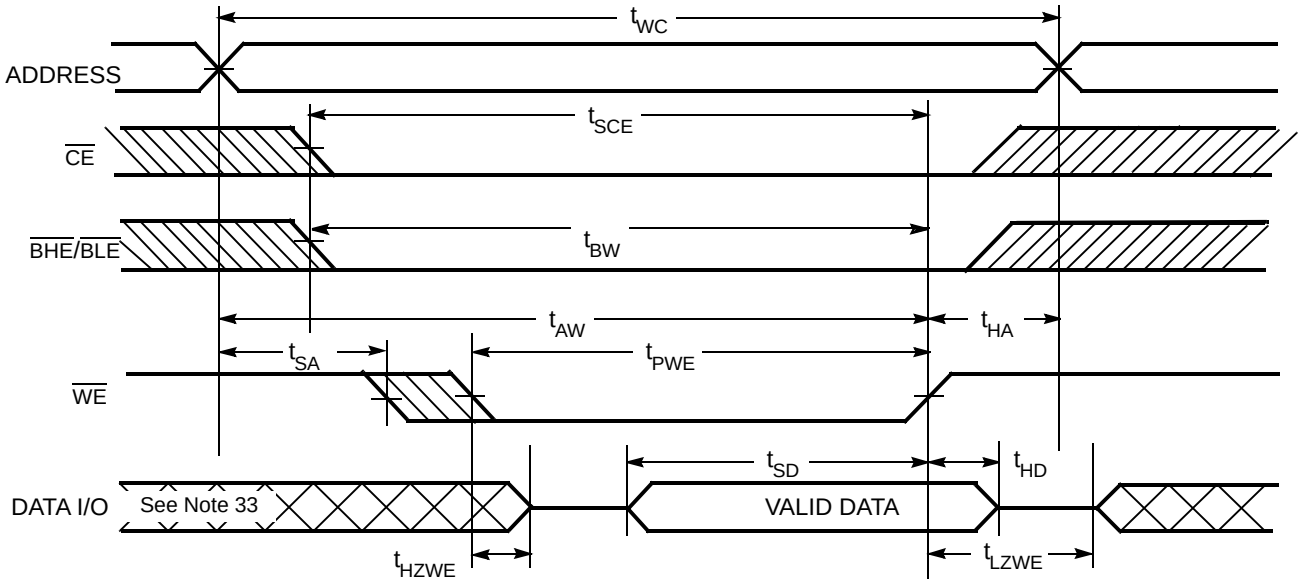
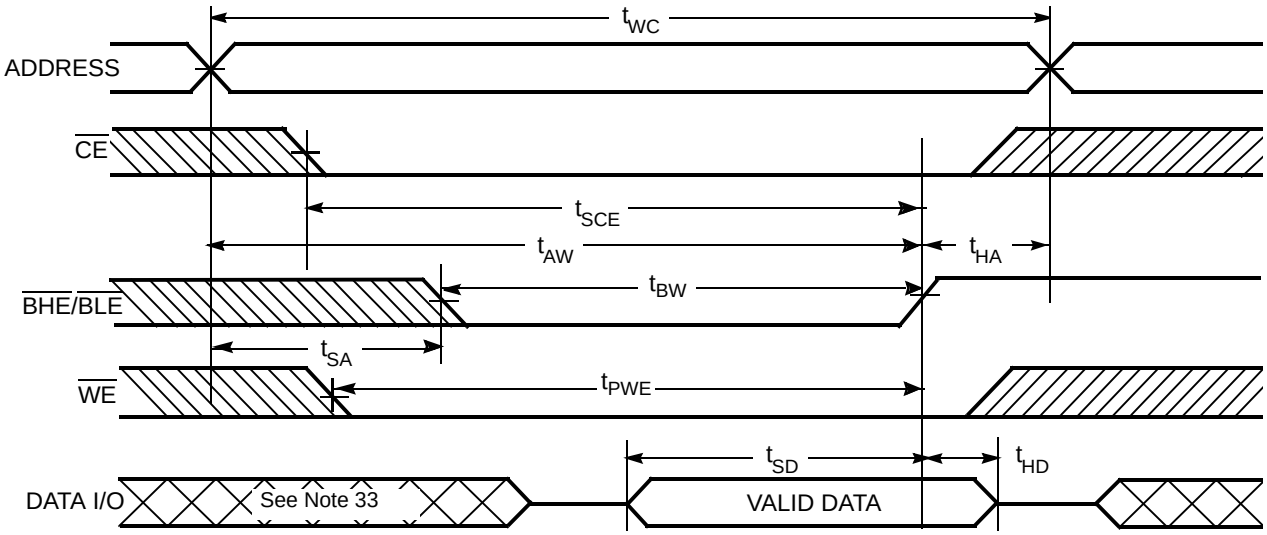


Figure 9. Write Cycle No. 4 (BHE/BLE Controlled) [29, 30, 31]



Notes
29. All Read/Write switching waveforms are shown for 16-bit data transactions only.
30. CE is the logical combination of CE_1 and CE_2. When CE_1 is LOW and CE_2 is HIGH, CE is LOW; when CE_1 is HIGH or CE_2 is LOW, CE is HIGH.
31. If CE goes HIGH simultaneously with WE = V_{IH}, the output remains in a high-impedance state.
32. The minimum write cycle pulse width should be equal to the sum of t_{SD} and t_{HZWE}.
33. During this period, the I/Os are in output state and input signals should not be applied.

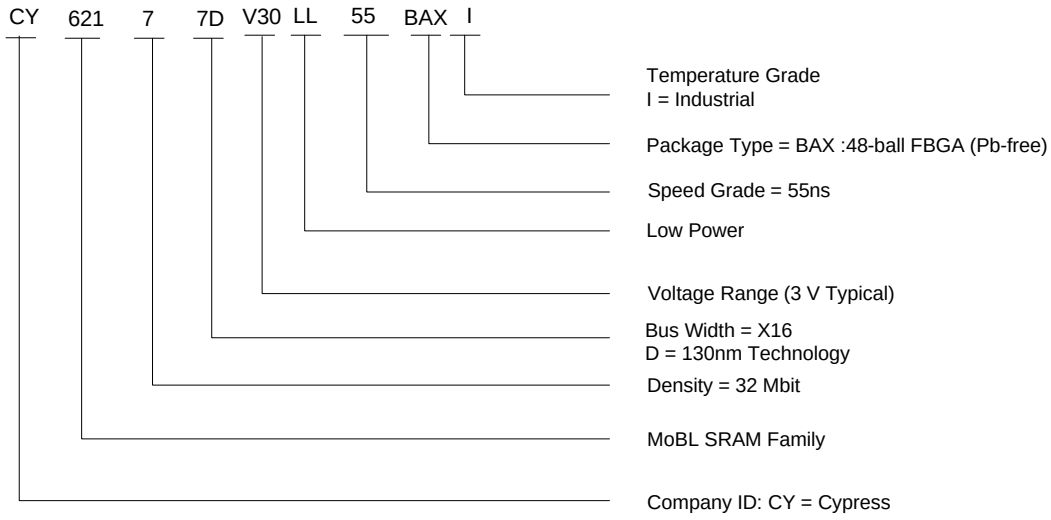
Truth Table

$\overline{CE_1}$	CE_2	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	X	High Z	Deselect/power-down	Standby (I_{SB})
X	L	X	X	X	X	High Z	Deselect/power-down	Standby (I_{SB})
X	X	X	X	H	H	High Z	Deselect/power-down	Standby (I_{SB})
L	H	H	L	L	L	Data out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	H	L	H	L	Data out (I/O_0–I/O_7); High Z (I/O_8–I/O_{15})	Read	Active (I_{CC})
L	H	H	L	L	H	High Z (I/O_0–I/O_7); Data Out (I/O_8–I/O_{15})	Read	Active (I_{CC})
L	H	H	H	L	H	High Z	Output disabled	Active (I_{CC})
L	H	H	H	H	L	High Z	Output disabled	Active (I_{CC})
L	H	H	H	L	L	High Z	Output disabled	Active (I_{CC})
L	H	L	X	L	L	Data in (I/O_0–I/O_{15})	Write	Active (I_{CC})
L	H	L	X	H	L	Data in (I/O_0–I/O_7); High Z (I/O_8–I/O_{15})	Write	Active (I_{CC})
L	H	L	X	L	H	High Z (I/O_0–I/O_7); Data in (I/O_8–I/O_{15})	Write	Active (I_{CC})

Ordering Information

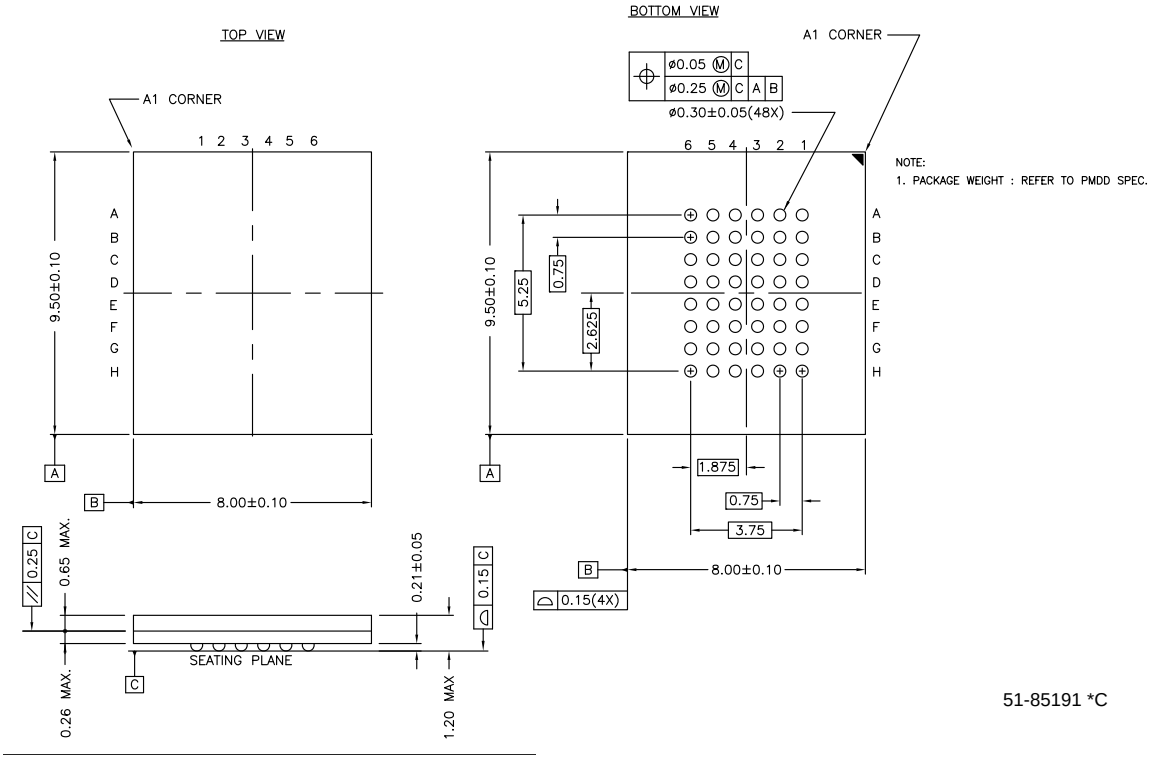
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
55	CY62177DV30LL-55BAXI	51-85191	48-ball FBGA (8 mm × 9.5 mm × 1.2 mm) (Pb-free)	Industrial

Ordering Code Definitions



Package Diagram

Figure 10. 48 ball FBGA (8 × 9.5 × 1.2 mm) Package Outline, 51-85191



Acronyms

Acronym	Description
CMOS	complementary metal oxide semiconductor
FBGA	fine ball grid array
I/O	input/output
SRAM	static random access memory

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
MHz	megahertz
µA	microampere
mA	milliampere
ns	nanosecond
pF	picofarad
V	volt
Ω	ohm
W	watt

Document History Page

Document Title: CY62177DV30 MoBL®, 32-Mbit (2M × 16) Static RAM Document #: 38-05633				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	251075	AJU	See ECN	New data sheet.
*A	330363	AJU	See ECN	Updated Document Title (Replaced CYM62177DV30 with CY62177DV30). Added second chip enable (CE_2) related information in all instances across the document. Updated Switching Characteristics: Added Note 12 and referred the same note in “Parameter” column.
*B	400960	NXR	See ECN	Changed address of Cypress Semiconductor Corporation on Page 1 from “3901 North First Street” to “198 Champion Court”. Updated Electrical Characteristics: Changed maximum value of I_{SB1} parameter from 60 and 40 μA to 100 μA corresponding to L and LL versions for both the 55 and the 70 ns speed bins respectively.
*C	469187	NXR	See ECN	Changed status from Preliminary to Final. Updated Electrical Characteristics: Changed maximum value of I_{SB2} parameter from 40 μA to 50 μA corresponding to LL version for both 45 ns and 55 ns speed bins. Updated Data Retention Characteristics: Changed maximum value of I_{CCDR} parameter from 20 μA to 25 μA for LL version. Updated Ordering Information.
*D	2896036	AJU	03/19/10	Updated Ordering Information (Removed inactive parts). Updated Package Diagram. Updated to new template.
*E	3153110	RAME	01/25/2011	Removed CY62177DV30L related information in all instances across the document. Removed 70 ns speed bin related information in all instances across the document. Added Ordering Code Definitions Updated to new template.
*F	3329873	RAME	07/27/11	Updated Functional Description: Removed Note “For best practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com website.” and its reference. Updated Capacitance: Removed Note “This applies for all packages.” and its reference in “Parameter” column (because of single package availability). Added Acronyms and Units of Measure. Updated template and styles according to current Cypress standards.
*G	3685455	MEMJ	07/20/2012	Updated Switching Waveforms: Added Note 18 and referred the same note in all waveforms. Updated text in Switching Waveforms diagrams. Updated Package Diagram.
*H	4576526	MEMJ	11/21/2014	Updated Functional Description: Added “For a complete list of related documentation, click here.” at the end. Updated Switching Characteristics: Added Note 17 and referred the same note in “Write Cycle”. Updated Switching Waveforms: Added Note 32 and referred the same note in Figure 8. Updated Package Diagram: spec 51-85191 – Changed revision from *B to *C.

Document History Page (continued)

Document Title: CY62177DV30 MoBL®, 32-Mbit (2M × 16) Static RAM Document #: 38-05633				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
*I	4919314	VINI	09/14/2015	Updated Switching Waveforms: Updated caption of Figure 9 (Removed "$\overline{OE}$ LOW"). Updated to new template. Completing Sunset Review.
*J	5444220	VINI	09/21/2016	Updated Thermal Resistance: Updated all values of θ_{JA} and θ_{JC} parameters. Updated to new template. Completing Sunset Review.

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Technical Support

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